

DBV 5 DBV 6 YEQ

TPS79301, TPS79318 TPS79325, TPS79328, TPS793285 TPS79330, TPS79333, TPS793475

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ULTRALOW-NOISE, HIGH PSRR, FAST RF 200-mA LOW-DROPOUT LINEAR REGULATORS IN NANOSTAR™ WAFER CHIP SCALE AND SOT23

FEATURES

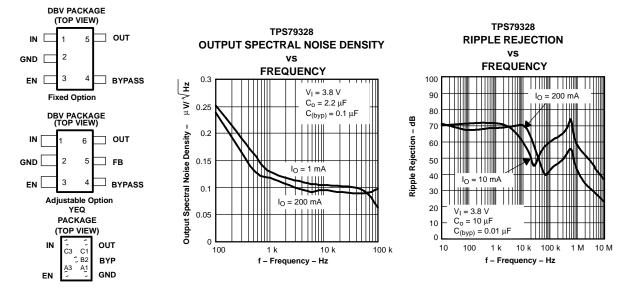
- 200-mA RF Low-Dropout Regulator With Enable
- Available in 1.8-V, 2.5-V, 2.8-V, 2.85-V, 3-V, 3.3-V, 4.75-V, and Adj (1.22 V to 5.5 V)
- High PSRR (70 dB at 10 kHz)
- Ultralow Noise (32 µV)
- Fast Start-Up Time (50 µs)
- Stable With a 2.2-µF Ceramic Capacitor
- Excellent Load/Line Transient Response
- Very Low Dropout Voltage (112 mV at Full Load, TPS79330)
- 5-Pin SOT23 (DBV) and NanoStar Wafer Chip Scale (YEQ) Packages

APPLICATIONS

- RF: VCOs, Receivers, ADCs
- Audio
- Cellular and Cordless Telephones
- Bluetooth[™], Wireless LAN
- Handheld Organizers, PDAs

DESCRIPTION

The TPS793xx family of low-dropout (LDO) low-power linear voltage regulators features high power supply rejection ratio (PSRR), ultralow noise, fast start-up, and excellent line and load transient responses in NanoStar wafer chip scale and SOT23 packages. NanoStar packaging gives an ultrasmall footprint as well as an ultralow profile and package weight, making it ideal for portable applications such as handsets and PDAs. Each device in the family is stable, with a small 2.2-µF ceramic capacitor on the output. The TPS793xx family uses an advanced, proprietary BiCMOS fabrication process to yield extremely low dropout voltages (e.g., 112 mV at 200 mA, TPS79330). Each device achieves fast start-up times (approximately 50 µs with a 0.001-µF bypass capacitor) while consuming very low quiescent current (170 µA typical). Moreover, when the device is placed in standby mode, the supply current is reduced to less than 1 µA. The TPS79328 exhibits approximately 32 µV_{RMS} of output voltage noise with a 0.1-µF bypass capacitor. Applications with analog components that are noise sensitive, such as portable RF electronics, benefit from the high PSRR and low-noise features as well as the fast response time.





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AVAILABLE OPTIONS⁽¹⁾

Т _Ј	VOLTAGE	PACKAGE	PART NUMBER	SYMBOL
	1.22 to 5.5 V		TPS79301DBVR	PGVI
	1.8 V	SOT23 (DBV)	TPS79318DBVR	PHHI
	1.8 V	CSP (YEQ)	TPS79318YEQ	E3
	2.5 V	SOT23 (DBV)	TPS79325DBVR	PGWI
-40°C to 125°C	2.5 V	CSP (YEQ)	TPS79325YEQ	E4
	2.8 V	SOT23 (DBV)	TPS79328DBVR	PGXI
	2.8 V	CSP (YEQ)	TPS79328YEQ	E2
	2.85 V	SOT23 (DBV)	TPS793285DBVR	PHII
	2.85 V	CSP (YEQ)	TPS793285YEQ	E5
	3 V	SOT23 (DBV)	TPS79330DBVR	PGYI
	3 V	CSP (YEQ)	TPS79330YEQ	E6
	3.3 V		TPS79333DBVR	PHUI
	4.75 V	SOT23 (DBV)	TPS793475DBVR	PHJI

(1) DBVR indicates tape and reel of 3000 parts. YEQR indicates tape and reel of 3000 parts. YEQT indicates tape and reel of 250 parts.

ABSOLUTE MAXIMUM RATINGS

over operating temperature range (unless otherwise noted)⁽¹⁾

	UNIT
V _{IN} range	-0.3 V to 6 V
V _{EN} range	-0.3 V to V _{IN} + 0.3 V
V _{OUT} range	-0.3 V to 6 V
Peak output current	Internally limited
ESD rating, HBM	2 kV
ESD rating, CDM	500 V
Continuous total power dissipation	See Dissipation Ratings Table
Operating junction temperature range, DBV package	-40°C to 150°C
Operating junction temperature range, YEQ package	-40°C to 125°C
Storage temperature range, T _{stg}	-65°C to 150°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

DISSIPATION RATINGS TABLE

BOARD	PACKAGE	$R_{\Theta JC}$	$R_{\Theta JA}$	DERATING FACTOR ABOVE T _A = 25°C	T _A ≤ 25°C POWER RATING	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING
Low-K ⁽¹⁾	DBV	65°C/W	255°C/W	3.9 mW/°C	390 mW	215 mW	155 mW
High-K ⁽²⁾	DBV	65°C/W	180°C/W	5.6 mW/°C	560 mW	310 mW	225 mW
Low-K ⁽¹⁾	YEQ	27°C/W	255°C/W	3.9 mW/°C	390 mW	215 mW	155 mW
High-K ⁽²⁾	YEQ	27°C/W	190°C/W	5.3 mW/°C	530 mW	296 mW	216 mW

(1) The JEDEC low-K (1s) board design used to derive this data was a 3-inch x 3-inch, two layer board with 2 ounce copper traces on top of the board.

(2) The JEDEC high-K (2s2p) board design used to derive this data was a 3-inch x 3-inch, multilayer board with 1 ounce internal power and ground planes and 2 ounce copper traces on top and bottom of the board.



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ELECTRICAL CHARACTERISTICS

over recommended operating temperature range T_J = -40 to 125 °C, V_{EN} = V_{IN}, V_{IN} = V_{OUT(nom)} + 1 V⁽¹⁾, I_{OUT} = 1 mA, C_{OUT} = 10 μ F, C_{BYPASS} = 0.01 μ F (unless otherwise noted). Typical values are at 25°C.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT	
V _{IN} Input voltage ⁽¹⁾				2.7		5.5	V	
I _{OUT} Continuous output current				0		200	mA	
V _{FB} Internal reference (TPS79	301)			1.201	1.225	1.250	V	
Output voltage range (TPS793	301)			V _{FB}		5.5 - V _{DO}	V	
T _J Operating junction tempera	ture			-40		125	°C	
	TPS79318	0 μA < I _{OUT} < 200 mA,	$2.8 \text{ V} < \text{V}_{\text{IN}} < 5.5 \text{ V}$	1.764	1.8	1.836	V	
	TPS79325	0 μA < I _{OUT} < 200 mA,	3.5 V < V _{IN} < 5.5 V	2.45	2.5	2.55	V	
	TPS79328	0 μA < I _{OUT} < 200 mA,	$3.8 \text{ V} < \text{V}_{\text{IN}} < 5.5 \text{ V}$	2.744	2.8	2.856	V	
Output voltage	TPS793285	0 μA < I _{OUT} < 200 mA,	$3.85 \text{ V} < \text{V}_{IN} < 5.5 \text{ V}$	2.793	2.85	2.907	V	
	TPS79330	0 μA < I _{OUT} < 200 mA,	4 V < V _{IN} < 5.5 V	2.94	3	3.06	V	
	TPS79333	$0 \ \mu A \le I_{OUT} < 200 \ mA$,	4.3 V < V _{IN} < 5.5 V	3.234	3.3	3.366	V	
	TPS793475	0 μA < I _{OUT} < 200 mA,	5.25 V < V _{IN} < 5.5 V	4.655	4.75	4.845	V	
Quiescent current (GND curre	nt)	0 µA < I _{OUT} < 200 mA			170	220	μA	
Load regulation (ΔV _{OUT} %/I _{OUT})	0 μA < I _{OUT} < 200 mA,	T _J = 25°C		5		mV	
Line regulation (ΔV _{OUT} %/V _{IN})	(1)	V _{OUT} + 1 V < V _{IN} ≤ 5.5 V			0.05	0.12	%/V	
			$C_{BYPASS} = 0.001 \ \mu F$		55			
Output asias usltans (TDC702	20)	BW = 200 Hz to 100 kHz, I _{OUT} = 200 mA	$C_{BYPASS} = 0.0047 \ \mu F$		36			
Output noise voltage (TPS793	28)		C _{BYPASS} = 0.01 µF		33		μV _{RMS}	
			C _{BYPASS} = 0.1 µF		32			
			C _{BYPASS} = 0.001 µF		50			
Time, start-up (TPS79328)		$R_L = 14 \Omega, C_{OUT} = 1 \mu F$ $C_{BYPASS} = 0.0047 \mu F$			70		μs	
			C _{BYPASS} = 0.01 µF		100		1	
Output current limit		V _{OUT} = 0 V		285		600	mA	
Standby current		V _{EN} = 0 V, 2.7 V < V _{IN} < 5.5 V			0.07	1	μA	
High level enable input voltage	9	2.7 V < V _{IN} < 5.5 V		1.7		V _{IN}	V	
Low level enable input voltage		2.7 V < V _{IN} < 5.5 V		0	•	0.7	V	
Input current (EN)		$V_{EN} = 0$		-1		1	μA	
Input current (FB) (TPS79301))	FB = 1.8 V				1	μA	
	TPS79328	f = 100 Hz, T _J = 25°C,	I _{OUT} = 10 mA		70			
Device events ringle rejection		$f = 100 \text{ Hz}, T_J = 25^{\circ}\text{C}, \qquad I_{OUT} = 200 \text{ mA}$ $f = 10 \text{ kHz}, T_J = 25^{\circ}\text{C}, \qquad I_{OUT} = 200 \text{ mA}$			68		dB	
Power supply ripple rejection					70			
		f = 100 kHz, T _J = 25°C,	I _{OUT} = 200 mA		43		1	
- (2)	TPS79328	I _{OUT} = 200 mA			120	200)) mV	
	TPS793285	I _{OUT} = 200 mA			120	200		
Dropout voltage ⁽²⁾ ($V_{IN} = V_{OUT(typ)} - 0.1V$)	TPS79330	I _{OUT} = 200 mA			112	200		
(VIN - VOUT(typ) - 0.1V)	TPS79333	I _{OUT} = 200 mA	1		102	180		
	TPS793475	I _{OUT} = 200 mA	1		77	125		
UVLO threshold		V _{CC} rising		2.25		2.65	V	
UVLO hysteresis					100		mV	

(1)

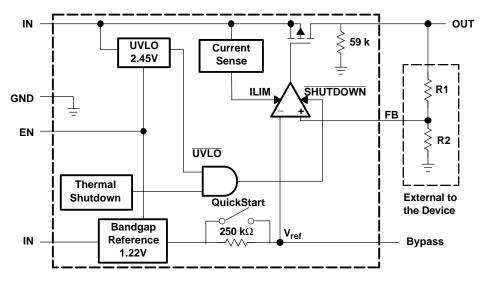
Minimum VIN is 2.7 V or V_{OUT} + V_{DO}, whichever is greater. Dropout is not measured for the TPS79318 and TPS79325 since minimum V_{IN} = 2.7 V. (2)



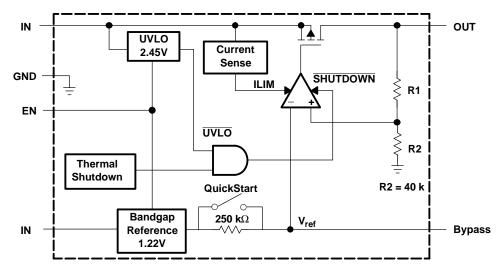
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FUNCTIONAL BLOCK DIAGRAMS

ADJUSTABLE VERSION



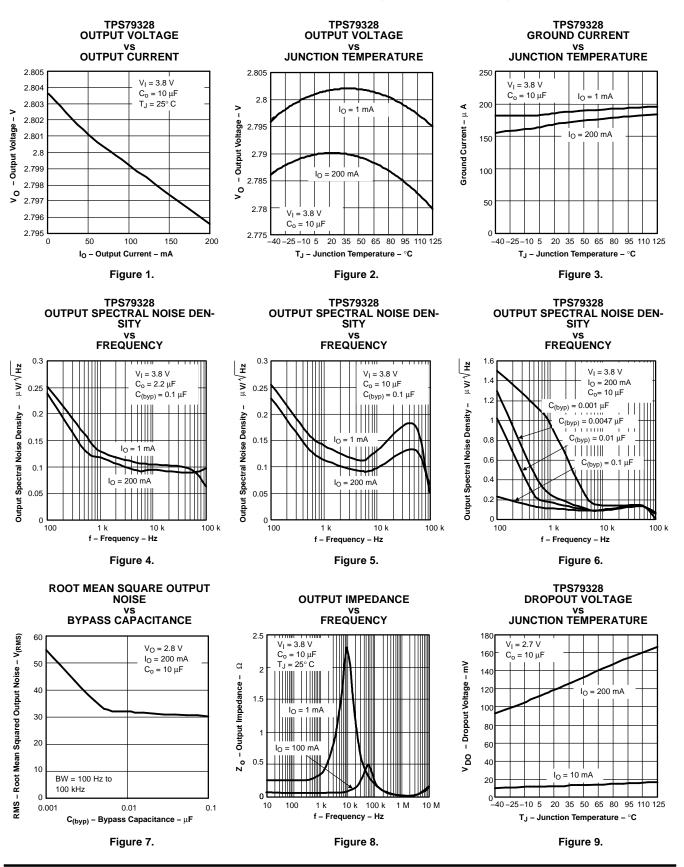
FIXED VERSION



Terminal Functions

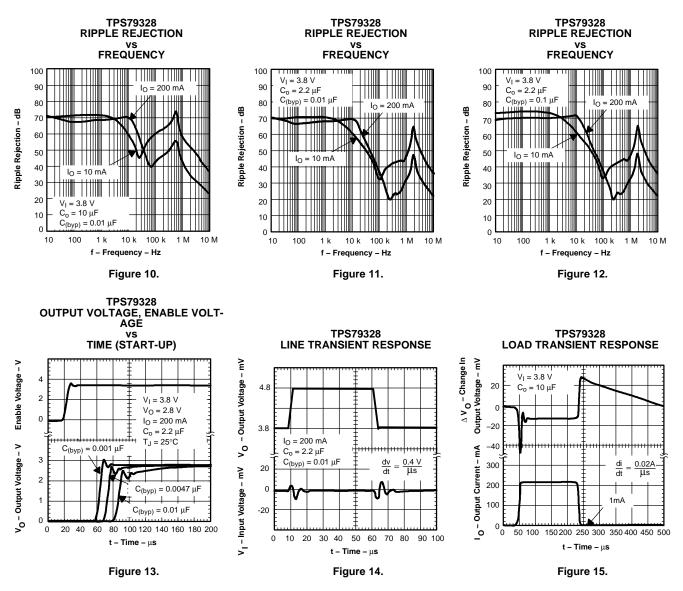
TERMINAL						
NAME	SOT23 ADJ	SOT23 FIXED	CSP FIXED	DESCRIPTION		
BYPASS	4	4	B2	An external bypass capacitor, connected to this terminal in conjunction with an internal resistor, creates a low-pass filter to further reduce regulator noise.		
EN	3	3	A3	The EN terminal is an input which enables or shuts down the device. When EN goes to a logic high, the device will be enabled. When the device goes to a logic low, the device is in shutdown mode.		
FB	5	N/A	N/A	This terminal is the feedback input voltage for the adjustable device.		
GND	2	2	A1	Regulator ground		
IN	1	1	C3	Unregulated input to the device.		
OUT	6	5	C1	Output of the regulator.		

TYPICAL CHARACTERISTICS (SOT23 PACKAGE)



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TYPICAL CHARACTERISTICS (SOT23 PACKAGE) (continued)

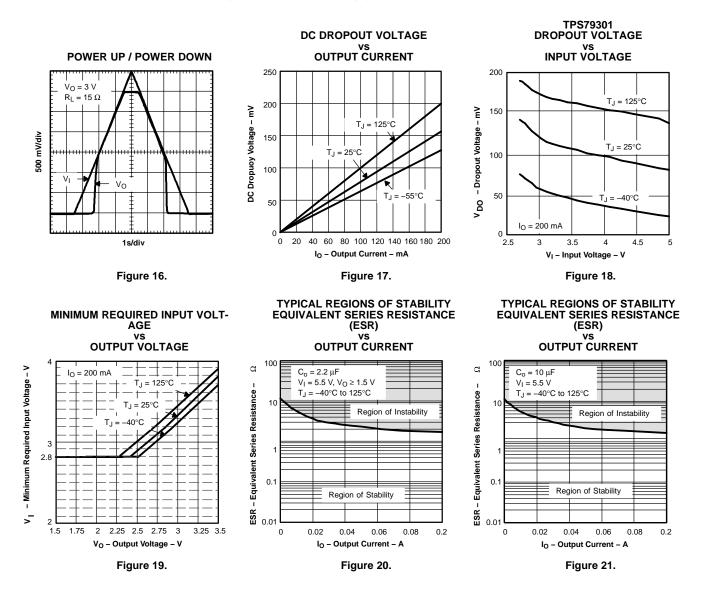


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TYPICAL CHARACTERISTICS (SOT23 PACKAGE) (continued)



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APPLICATION INFORMATION

The TPS793xx family of low-dropout (LDO) regulators has been optimized for use in noise-sensitive battery-operated equipment. The device features extremely low dropout voltages, high PSRR, ultralow output noise, low quiescent current (170 μ A typically), and enable-input to reduce supply currents to less than 1 μ A when the regulator is turned off.

A typical application circuit is shown in Figure 22.

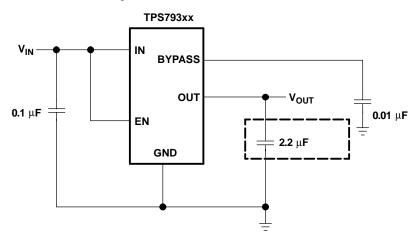


Figure 22. Typical Application Circuit

External Capacitor Requirements

A 0.1- μ F or larger ceramic input bypass capacitor, connected between IN and GND and located close to the TPS793xx, is required for stability and improves transient response, noise rejection, and ripple rejection. A higher-value input capacitor may be necessary if large, fast-rise-time load transients are anticipated or the device is located several inches from the power source.

Like most low dropout regulators, the TPS793xx requires an output capacitor connected between OUT and GND to stabilize the internal control loop. The minimum recommended capacitance is 2.2 μ F. Any 2.2- μ F or larger ceramic capacitor is suitable, provided the capacitance does not vary significantly over temperature. If load current is not expected to exceed 100 mA, a 1.0- μ F ceramic capacitor can be used.

The internal voltage reference is a key source of noise in an LDO regulator. The TPS793xx has a BYPASS pin which is connected to the voltage reference through a 250-k Ω internal resistor. The 250-k Ω internal resistor, in conjunction with an external bypass capacitor connected to the BYPASS pin, creates a low pass filter to reduce the voltage reference noise and, therefore, the noise at the regulator output. In order for the regulator to operate properly, the current flow out of the BYPASS pin must be at a minimum, because any leakage current creates an IR drop across the internal resistor thus creating an output error. Therefore, the bypass capacitor must have minimal leakage current. The bypass capacitor should be no more than 0.1- μ F to ensure that it is fully charged during the quickstart time provided by the internal switch shown in the Functional Block Diagrams

As an example, the TPS79328 exhibits only 32 μV_{RMS} of output voltage noise using a 0.1- μ F ceramic bypass capacitor and a 2.2- μ F ceramic output capacitor. Note that the output starts up slower as the bypass capacitance increases due to the RC time constant at the BYPASS pin that is created by the internal 250-k Ω resistor and external capacitor.

Board Layout Recommendation to Improve PSRR and Noise Performance

To improve ac measurements like PSRR, output noise, and transient response, it is recommended that the board be designed with separate ground planes for V_{IN} and V_{OUT} , with each ground plane connected only at the GND pin of the device. In addition, the ground connection for the bypass capacitor should connect directly to the GND pin of the device.

APPLICATION INFORMATION (continued)

Power Dissipation and Junction Temperature

Specified regulator operation is assured to a junction temperature of 125°C; the maximum junction temperature should be restricted to 125°C under normal operating conditions. This restriction limits the power dissipation the regulator can handle in any given application. To ensure the junction temperature is within acceptable limits, calculate the maximum allowable dissipation, $P_{D(max)}$, and the actual dissipation, P_D , which must be less than or equal to $P_{D(max)}$.

The maximum power dissipation limit is determined using Equation 1:

$$\mathsf{P}_{\mathsf{D}(\mathsf{max})} = \frac{\mathsf{T}_{\mathsf{J}} \max - \mathsf{T}_{\mathsf{A}}}{\mathsf{R}_{\mathsf{\Theta}\mathsf{J}\mathsf{A}}} \tag{1}$$

Where:

- T_Jmax is the maximum allowable junction temperature.
- R_{0JA} is the thermal resistance junction-to-ambient for the package (see the Dissipation Ratings Table).
- T_A is the ambient temperature.

The regulator dissipation is calculated using Equation 2:

$$\mathbf{P}_{\mathrm{D}} = (\mathbf{V}_{\mathrm{IN}} - \mathbf{V}_{\mathrm{OUT}}) \times \mathbf{I}_{\mathrm{OUT}}$$

Power dissipation resulting from quiescent current is negligible. Excessive power dissipation triggers the thermal protection circuit.

Programming the TPS79301 Adjustable LDO Regulator

The output voltage of the TPS79301 adjustable regulator is programmed using an external resistor divider as shown in Figure 23. The output voltage is calculated using Equation 3:

$$V_{OUT} = V_{REF} \times \left(1 + \frac{R_1}{R_2}\right)$$
(3)

Where:

• $V_{REF} = 1.2246$ V typ (the internal reference voltage)

Resistors R1 and R2 should be chosen for approximately 50- μ A divider current. Lower value resistors can be used for improved noise performance, but the solution consumes more power. Higher resistor values should be avoided as leakage current into/out of FB across R1/R2 creates an offset voltage that artificially increases/decreases the feedback voltage and thus erroneously decreases/increases V_{OUT}. The recommended design procedure is to choose R2 = 30.1 k Ω to set the divider current at 50 μ A, C1 = 15 pF for stability, and then calculate R1 using Equation 4:

$$R_{1} = \left(\frac{V_{OUT}}{V_{ref} - 1}\right) \times R_{2}$$
(4)

In order to improve the stability of the adjustable version, it is suggested that a small compensation capacitor be placed between OUT and FB. For voltages <1.8 V, the value of this capacitor should be 100 pF. For voltages >1.8 V, the approximate value of this capacitor can be calculated as shown in Equation 5:

$$C_{1} = \frac{(3 \times 10^{-7}) \times (R_{1} + R_{2})}{(R_{1} \times R_{2})}$$
(5)

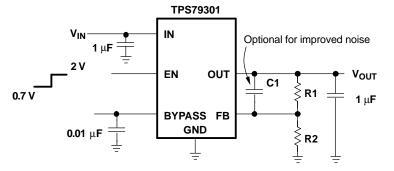
The suggested value of this capacitor for several resistor ratios is shown in the table below. If this capacitor is not used (such as in a unity-gain configuration) or if an output voltage <1.8 V is chosen, then the minimum recommended output capacitor is 4.7 μ F instead of 2.2 μ F.

(2)



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APPLICATION INFORMATION (continued)



OUTPUT VOLTAGE PROGRAMMING GUIDE

OUTPUT VOLTAGE	R1	R2	C1	
1.22 V	short	open	0 pF	
2.5 V	31.6 k Ω	30.1 k Ω	22 pF	
3.3 V	51 kΩ	30.1 k Ω	15 pF	
3.6 V	59 k Ω	30.1 k Ω	15 pF	

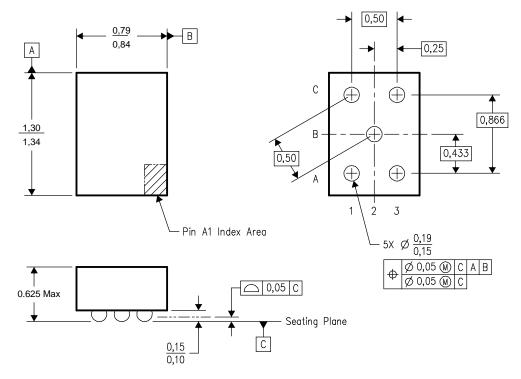
Regulator Protection

The TPS793xx PMOS-pass transistor has a built-in back diode that conducts reverse current when the input voltage drops below the output voltage (e.g., during power down). Current is conducted from the output to the input and is not internally limited. If extended reverse voltage operation is anticipated, external limiting might be appropriate.

The TPS793xx features internal current limiting and thermal protection. During normal operation, the TPS793xx limits output current to approximately 400 mA. When current limiting engages, the output voltage scales back linearly until the overcurrent condition ends. While current limiting is designed to prevent gross device failure, care should be taken not to exceed the power dissipation ratings of the package or the absolute maximum voltage ratings of the device. If the temperature of the device exceeds approximately 165°C, thermal-protection circuitry shuts it down. Once the device has cooled down to below approximately 140°C, regulator operation resumes.



APPLICATION INFORMATION (continued) TPS793xxYEQ NanoStar™ Wafer Chip Scale Information



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

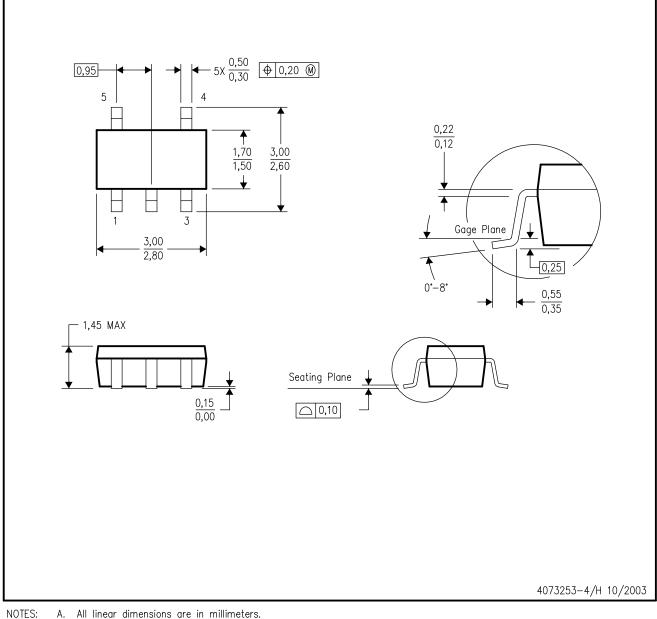
- C. NanoStar™ package configuration.
- D. This package is tin-lead (SnPb), consult the factory for availability of lead-free material.

NanoStar is a trademark of Texas Instruments.

Figure 24. NanoStar™ Wafer Chip Scale Package

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE

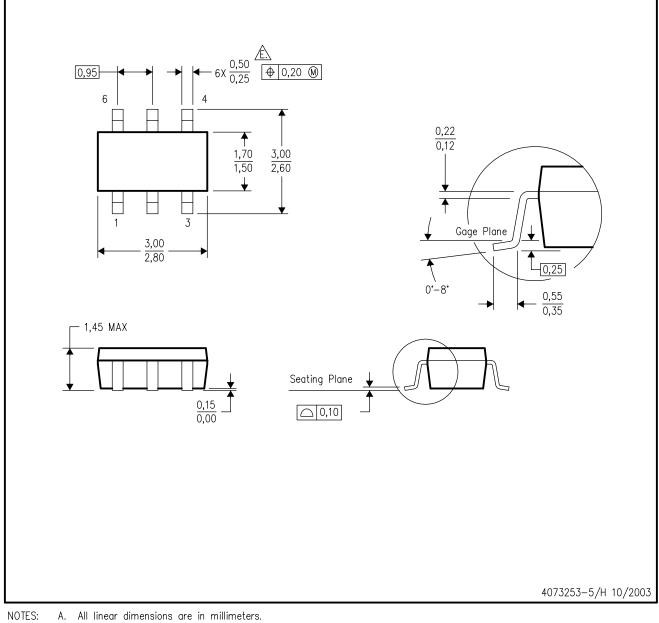


- Α. All linear dimensions are in millimeters.
 - Β. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold fla D. Falls within JEDEC MO-178 Variation AA. Body dimensions do not include mold flash or protrusion.



DBV (R-PDSO-G6)

PLASTIC SMALL-OUTLINE PACKAGE

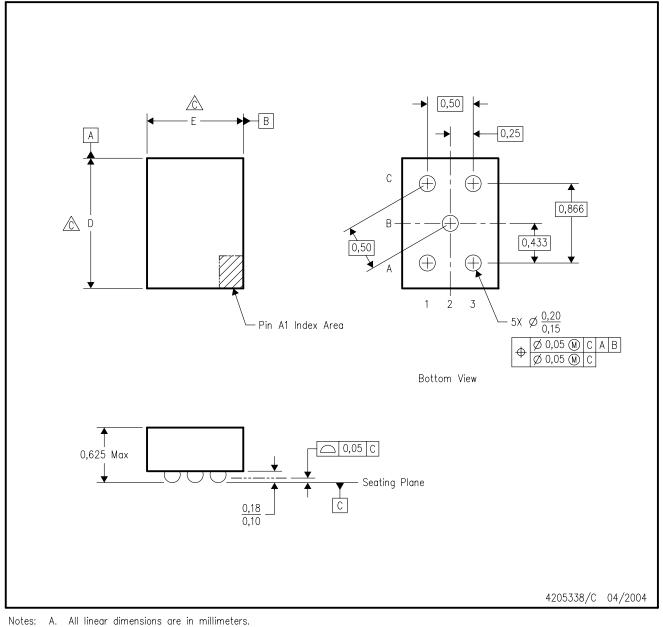


- Β. This drawing is subject to change without notice.
- Body dimensions do not include mold flash or protrusion.
- C. D. Leads 1,2,3 may be wider than leads 4,5,6 for package orientation.
- E Falls within JEDEC MO-178 Variation AB, except minimum lead width.



YEQ (R-XBGA-N5)

DIE-SIZE BALL GRID ARRAY



- B. This drawing is subject to change without notice.
- Devices in this YEQ package can have dimension D ranging from 1.17 to 1.67 and dimension E ranging from 0.80 to 1.30. To determine the exact package size of a particular device, refer to the device datasheet or contact a local TI representative.
- D. NanoStar™ package configuration.
- E. This package contains tin-lead (SnPb) balls. Refer to the 5 YZQ package (drawing 4205677) for lead-free balls.

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